74CBTLV3257

Quad 1-of-2 multiplexer/demultiplexer

Rev. 01. — 02 October 2009 Preliminary data sheet

1. General description

The 74CBTLV3257 provides a quad 1-of-2 high-speed multiplexer/demultiplexer with a common select input (S) and an output enable input ($\overline{OE}$). The low ON resistance of the switch allows inputs to be connected to outputs without adding propagation delay or generating additional ground bounce noise. When pin $\overline{OE}$ = LOW, one of the two switches is selected (low-impedance ON-state) with pin S. When pin $\overline{OE}$ = HIGH, all switches are in the high-impedance OFF-state, independent of pin S.

Schmitt trigger action at control input makes the circuit tolerant to slower input rise and fall times across the entire V_{CC} range from 2.3 V to 3.6 V.

To ensure the high-impedance OFF-state during power-up or power-down, $\overline{OE}$ should be tied to the V_{CC} through a pull-up resistor. The minimum value of the resistor is determined by the current-sinking capability of the driver.

This device is fully specified for partial power-down applications using I_{OFF}. The I_{OFF} circuitry disables the output, preventing the damaging backflow current through the device when it is powered down.

2. Features

- Supply voltage range from 2.3 V to 3.6 V
- High noise immunity
- Complies with JEDEC standard:
  - JESD8-5 (2.3 V to 2.7 V)
  - JESD8-B/JESD36 (2.7 V to 3.6 V)
- ESD protection:
  - HBM JESD22-A114E exceeds 2000 V
  - MM JESD22-A115-A exceeds 200 V
  - CDM AEC-Q100-011 revision B exceeds 1000 V
- 5 Ω switch connection between two ports
- Rail to rail switching on data I/O ports
- CMOS low power consumption
- Latch-up performance exceeds 250 mA per JESD78A Class I level A
- I_{OFF} circuitry provides partial Power-down mode operation
- Multiple package options
- Specified from –40 °C to +85 °C and –40 °C to +125 °C

founded by Philips

3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74CBTLV3257D	–40 °C to +125 °C	SO16	plastic small outline package; 16 leads; body width 3.9 mm	SOT109-1
74CBTLV3257DS	–40 °C to +125 °C	SSOP16[1]	plastic shrink small outline package; 16 leads; body width 3.9 mm; lead pitch 0.635 mm	SOT519-1
74CBTLV3257PW	–40 °C to +125 °C	TSSOP16	plastic thin shrink small outline package; 16 leads; body width 4.4 mm	SOT403-1
74CBTLV3257BQ	–40 °C to +125 °C	DHVQFN16	plastic dual-in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 × 3.5 × 0.85 mm	SOT763-1

[1] Also known as QSOP16.

4. Functional diagram

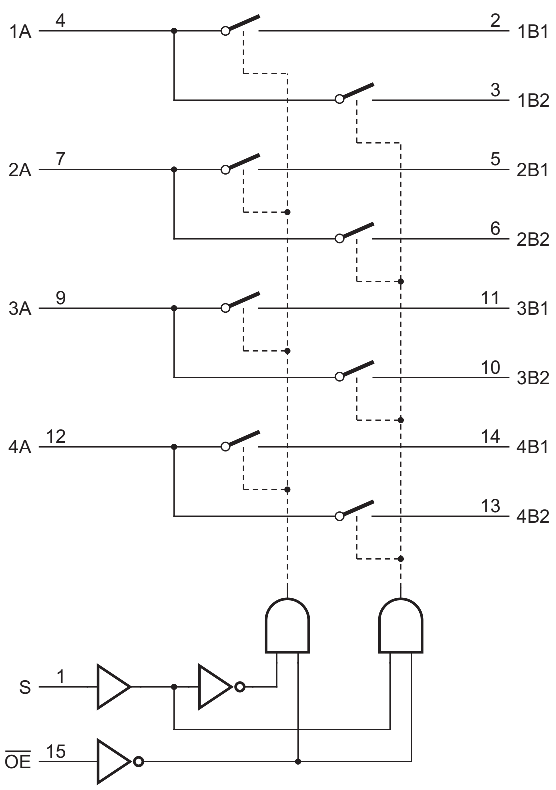


Fig 1. Logic diagram

5. Pinning information

5.1 Pinning

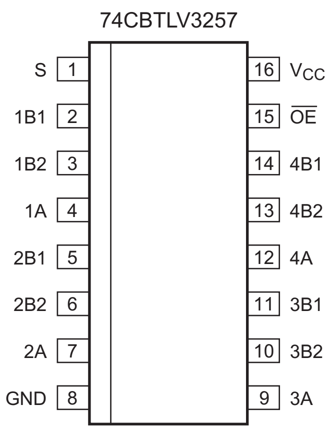


Fig 2. Pin configuration SOT109-1 (SO16) and SOT519-1 (SSOP16)

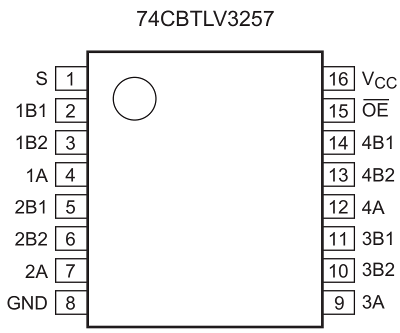
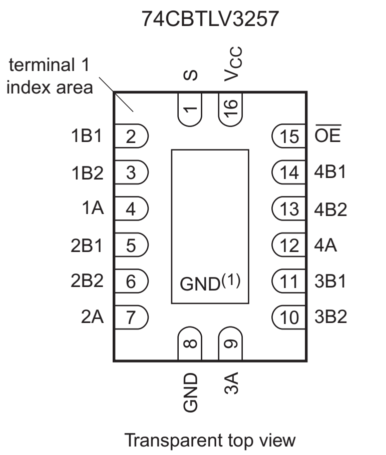


Fig 3. Pin configuration SOT403-1 (TSSOP16)



(1) The die substrate is attached to the exposed die pad using conductive die attach material. It can not be used as a supply pin or input.

Fig 4. Pin configuration SOT763-1 (DHVQFN16)

5.2 Pin description

Table 2. Pin description

Symbol	Pin	Description
S	1	select input
1B1 to 4B1	2, 5, 11, 14	B1 input/output
1B2 to 4B2	3, 6, 10, 13	B2 input/output
1A to 4A	4, 7, 9, 12	A input/output
GND	8	ground (0 V)
$\overline{OE}$	15	output enable input (active LOW)
V_{CC}	16	supply voltage

6. Functional description

Table 3. Function table[1]

Inputs		Function switch
$\overline{OE}$	S	
L	L	nA = nB1
L	H	nA = nB2
H	X	disconnect nA and nBn

[1] H = HIGH voltage level; L = LOW voltage level.

7. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			–0.5	+4.6	V
V_I	input voltage		[1]	–0.5	+4.6	V
V_{SW}	switch voltage	enable and disable mode	[1]	–0.5	V_{CC} + 0.5	V
I_{IK}	input clamping current	$V_{I/O}$ < –0.5 V		–50	-	mA
I_{SK}	switch clamping current	V_I < –0.5 V or V_I > V_{CC} + 0.5 V		-	±50	mA
I_{SW}	switch current	V_{SW} = 0 V to V_{CC}		-	±128	mA
I_{CC}	supply current			-	+100	mA
I_{GND}	ground current			–100	-	mA
T_{stg}	storage temperature			–65	+150	°C
P_{tot}	total power dissipation	T_{amb} = –40 °C to +125 °C	[2]	-	500	mW

[1] The minimum input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For SO16 packages: P_{tot} derates linearly with 8 mW/K above 70 °C.
For SSOP16 and TSSOP16 packages: P_{tot} derates linearly with 5.5 mW/K above 60 °C.
For DHVQFN16 packages: P_{tot} derates linearly with 4.5 mW/K above 60 °C.

8. Recommended operating conditions

Table 5. Recommended operating conditions

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CC}	supply voltage			2.3	3.6	V
V_I	input voltage			0	3.6	V
V_{SW}	switch voltage	enable and disable mode		0	V_{CC}	V
T_{amb}	ambient temperature			–40	+125	°C
$\Delta t/\Delta V$	input transition rise and fall rate	V_{CC} = 2.3 V to 3.6 V	[1]	0	200	ns/V

[1] Applies to control signal levels.

9. Static characteristics

Table 6. Static characteristics

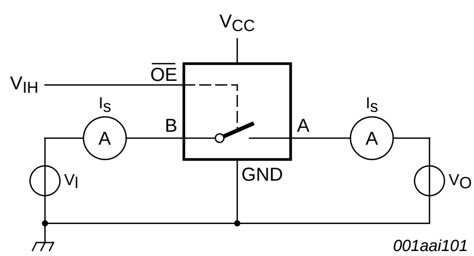
At recommended operating conditions voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	T_{amb} = −40 °C to +85 °C			T_{amb} = −40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
V_{IH}	HIGH-level input voltage	V_{CC} = 2.3 V to 2.7 V	1.7	-	-	1.7	-	V
		V_{CC} = 3.0 V to 3.6 V	2.0	-	-	2.0	-	V
V_{IL}	LOW-level input voltage	V_{CC} = 2.3 V to 2.7 V	-	-	0.7	-	0.7	V
		V_{CC} = 3.0 V to 3.6 V	-	-	0.9	-	0.9	V
I_I	input leakage current	pin $\overline{OE}$, S; V_I = GND to V_{CC}; V_{CC} = 3.6 V	-	-	±1	-	±20	μA
$I_{S(OFF)}$	OFF-state leakage current	V_I = V_{IH} or V_{IL}; V_{CC} = 3.6 V; see Figure 5	-	-	±1	-	±20	μA
$I_{S(ON)}$	ON-state leakage current	V_I = V_{IH} or V_{IL}; V_{CC} = 3.6 V; see Figure 6	-	-	±1	-	±20	μA
I_{OFF}	power-off leakage current	V_I or V_O = 0 V to 3.6 V; V_{CC} = 0 V	-	-	±10	-	±50	μA
I_{CC}	supply current	V_I = GND or V_{CC}; I_O = 0 A; V_{SW} = GND or V_{CC}; V_{CC} = 3.6 V	-	-	10	-	50	μA
ΔI_{CC}	additional supply current	pin $\overline{OE}$, S; V_I = V_{CC} − 0.6 V; V_{SW} = GND or V_{CC}; V_{CC} = 3.6 V [2]	-	-	300	-	2000	μA
C_I	input capacitance	pin $\overline{OE}$, S; V_{CC} = 3.3 V; V_I = 0 V to 3.3 V	-	0.9	-	-	-	pF
$C_{S(OFF)}$	OFF-state capacitance	V_{CC} = 3.3 V; V_I = 0 V to 3.3 V	-	5.2	-	-	-	pF
$C_{S(ON)}$	ON-state capacitance	V_{CC} = 3.3 V; V_I = 0 V to 3.3 V	-	14.3	-	-	-	pF

[1] All typical values are measured at T_{amb} = 25 °C.

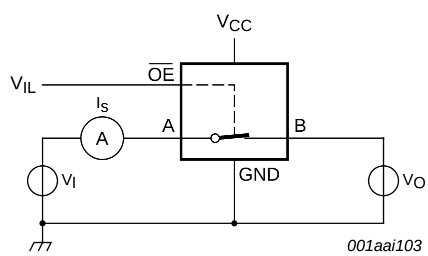
[2] One input at 3 V, other inputs at V_{CC} or GND.

9.1 Test circuits



V_I = V_{CC} or GND and V_O = GND or V_{CC}.

Fig 5. Test circuit for measuring OFF-state leakage current (one switch)



V_I = V_{CC} or GND and V_O = open circuit.

Fig 6. Test circuit for measuring ON-state leakage current (one switch)

9.2 ON resistance

Table 7. Resistance R_{ON}

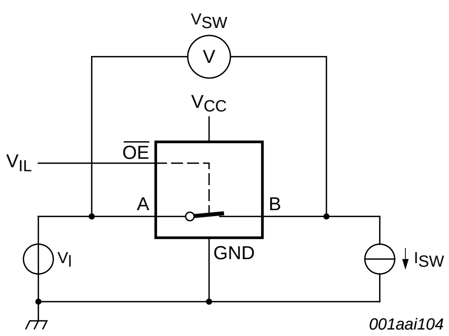
At recommended operating conditions; voltages are referenced to GND (ground = 0 V); for test circuit see Figure 7.

Symbol	Parameter	Conditions	T_{amb} = −40 °C to +85 °C			T_{amb} = −40 °C to +125 °C		Unit
			Min	Typ[1]	Max	Min	Max	
R_{ON}	ON resistance	V_{CC} = 2.3 V to 2.7 V; see Figure 8 to Figure 10 [2]						
		I_{SW} = 64 mA; V_I = 0 V	-	4.2	8.0	-	15.0	Ω
		I_{SW} = 24 mA; V_I = 0 V	-	4.2	8.0	-	15.0	Ω
		I_{SW} = 15 mA; V_I = 1.7 V	-	8.4	40	-	60.0	Ω
		V_{CC} = 3.0 V to 3.6 V; see Figure 11 to Figure 13						
		I_{SW} = 64 mA; V_I = 0 V	-	4.0	7.0	-	11.0	Ω
		I_{SW} = 24 mA; V_I = 0 V	-	4.0	7.0	-	11.0	Ω
		I_{SW} = 15 mA; V_I = 2.4 V	-	6.2	15	-	25.5	Ω

[1] Typical values are measured at T_{amb} = 25 °C and nominal V_{CC}.

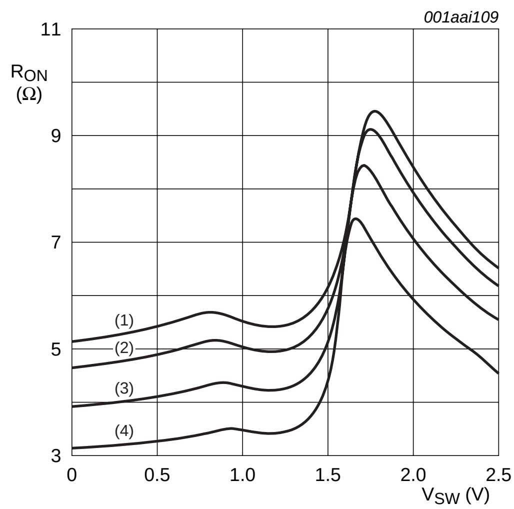
[2] Measured by the voltage drop between the A and B terminals at the indicated current through the switch. ON-state resistance is determined by the lower of the voltages of the two (A or B) terminals.

9.3 ON resistance test circuit and graphs



$R_{ON} = V_{SW} / I_{SW}$.

Fig 7. Test circuit for measuring ON resistance (one switch)



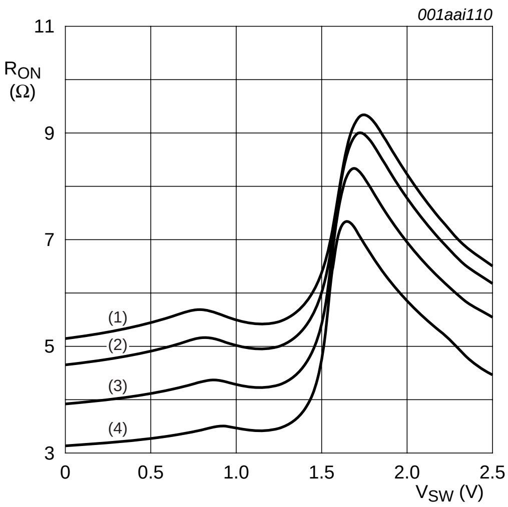
(1) T_{amb} = 125 °C.

(2) T_{amb} = 85 °C.

(3) T_{amb} = 25 °C.

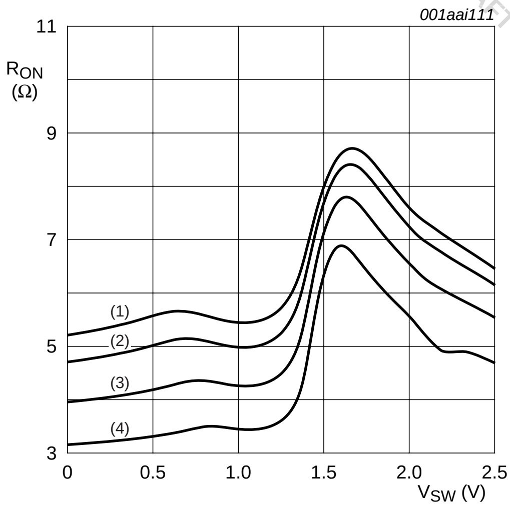
(4) T_{amb} = −40 °C.

Fig 8. ON resistance as a function of input voltage; V_{CC} = 2.5 V; I_{SW} = 15 mA; V_{SW} = 1.7 V



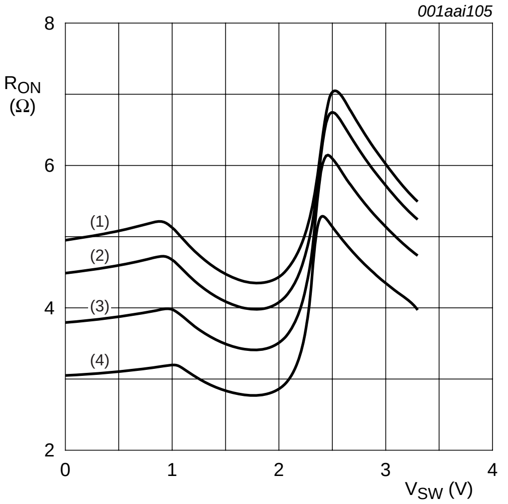
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 9. ON resistance as a function of input voltage; V_{CC} = 2.5 V; I_{SW} = 24 mA; V_{SW} = 0 V



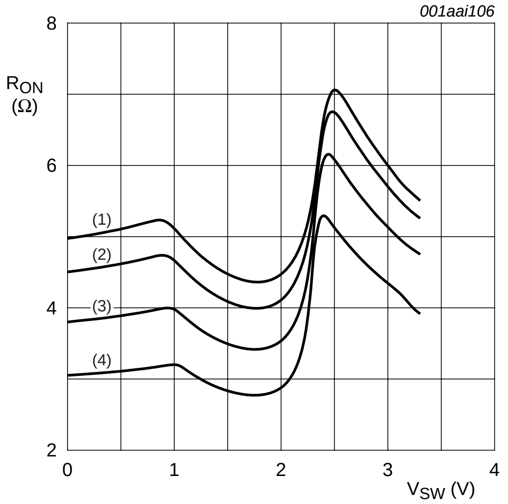
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 10. ON resistance as a function of input voltage; V_{CC} = 2.5 V; I_{SW} = 64 mA; V_{SW} = 1.7 V



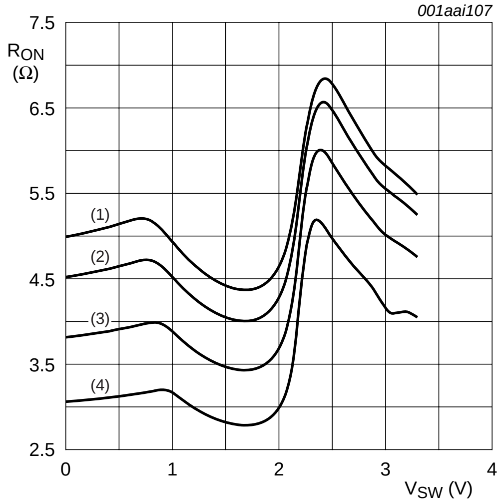
(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 11. ON resistance as a function of input voltage; V_{CC} = 3.3 V; I_{SW} = 15 mA; V_{SW} = 2.4 V



(1) T_{amb} = 125 °C.
(2) T_{amb} = 85 °C.
(3) T_{amb} = 25 °C.
(4) T_{amb} = −40 °C.

Fig 12. ON resistance as a function of input voltage; V_{CC} = 3.3 V; I_{SW} = 24 mA; V_{SW} = 0 V



(1) T_{amb} = 125 °C.

(2) T_{amb} = 85 °C.

(3) T_{amb} = 25 °C.

(4) T_{amb} = −40 °C.

Fig 13. ON resistance as a function of input voltage; V_{CC} = 3.3 V; I_{SW} = 64 mA; V_{SW} = 1.7 V

10. Dynamic characteristics

Table 8. Dynamic characteristics

GND = 0 V; for test circuit see Figure 16

Symbol	Parameter	Conditions		T_{amb} = −40 °C to +85 °C			T_{amb} = −40 °C to +125 °C		Unit
				Min	Typ[1]	Max	Min	Max	
t_{pd}	propagation delay	nA to nBn or nBn to nA; see Figure 14	[2][3]						
		V_{CC} = 2.3 V to 2.7 V		-	-	0.15	-	0.25	ns
		V_{CC} = 3.0 V to 3.6 V		-	-	0.15	-	0.25	ns
		S to nA; see Figure 14	[3]						
		V_{CC} = 2.3 V to 2.7 V		1.0	3.3	6.1	1.0	6.7	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.8	5.3	1.0	5.8	ns
t_{en}	enable time	$\overline{OE}$ to nA or nBn; see Figure 15	[4]						
		V_{CC} = 2.3 V to 2.7 V		1.0	2.2	5.6	1.0	6.2	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.0	5.0	1.0	5.5	ns
		S to nBn; see Figure 15							
		V_{CC} = 2.3 V to 2.7 V		1.0	3.3	6.1	1.0	6.7	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.7	5.3	1.0	5.8	ns
t_{dis}	disable time	$\overline{OE}$ to nA or nBn; see Figure 15	[5]						
		V_{CC} = 2.3 V to 2.7 V		1.0	2.6	5.5	1.0	6.1	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	3.1	5.5	1.0	6.1	ns
		S to nBn; see Figure 15							
		V_{CC} = 2.3 V to 2.7 V		1.0	2.7	4.8	1.0	5.3	ns
		V_{CC} = 3.0 V to 3.6 V		1.0	2.4	4.5	1.0	5.0	ns

[1] All typical values are measured at T_{amb} = 25 °C and at nominal V_{CC}.

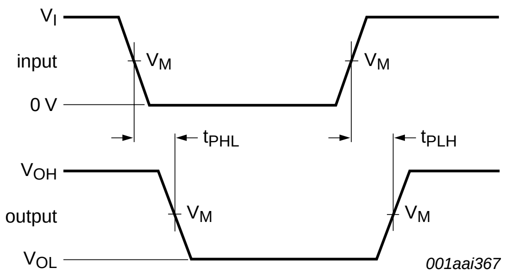
[2] The propagation delay is the calculated RC time constant of the maximum on-state resistance of the switch and the load capacitance, when driven by an ideal voltage source (zero output impedance).

[3] t_{pd} is the same as t_{PLH} and t_{PHL}.

[4] t_{en} is the same as t_{PZH} and t_{PZL}.

[5] t_{dis} is the same as t_{PHZ} and t_{PLZ}.

11. Waveforms



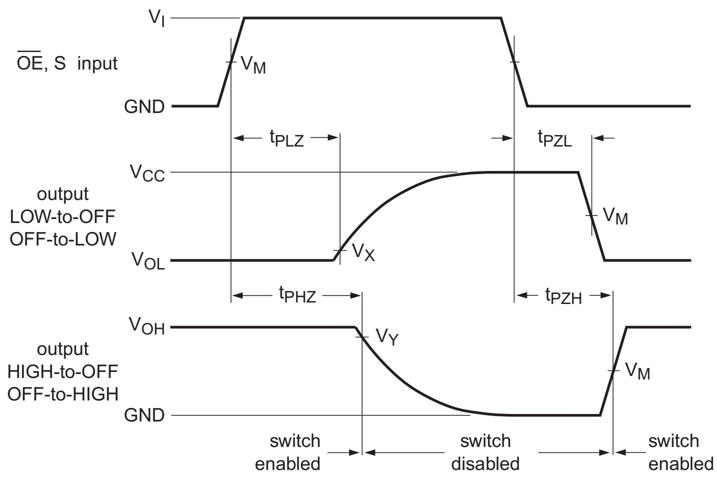
Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 14. The data input (nA or nBn) to output (nBn or nA) propagation delays

Table 9. Measurement points

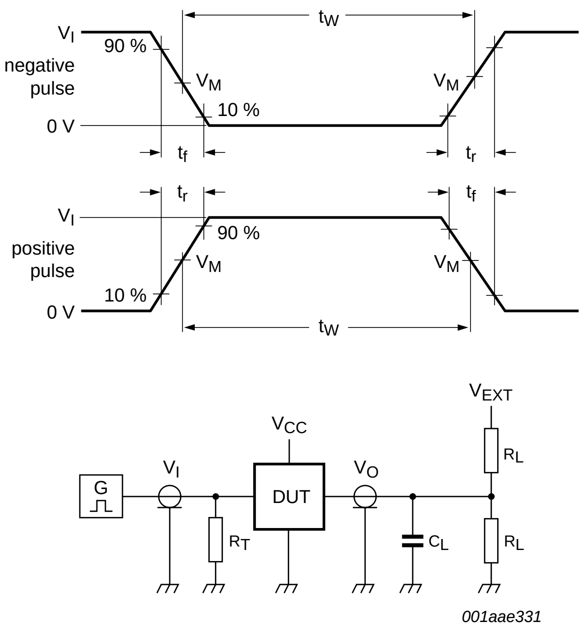
Supply voltage	Input			Output		
V_{CC}	V_M	V_I	$t_r = t_f$	V_M	V_X	V_Y
2.3 V to 2.7 V	$0.5V_{CC}$	V_{CC}	≤ 2.0 ns	$0.5V_{CC}$	V_{OL} + 0.15 V	V_{OH} − 0.15 V
3.0 V to 3.6 V	$0.5V_{CC}$	V_{CC}	≤ 2.0 ns	$0.5V_{CC}$	V_{OL} + 0.3 V	V_{OH} − 0.3 V



Measurement points are given in Table 9.

Logic levels: V_{OL} and V_{OH} are typical output voltage levels that occur with the output load.

Fig 15. Enable and disable times



Test data is given in Table 10.

Definitions for test circuit:

R_L = Load resistance.

C_L = Load capacitance including jig and probe capacitance.

R_T = Termination resistance should be equal to the output impedance Z_o of the pulse generator.

V_{EXT} = External voltage for measuring switching times.

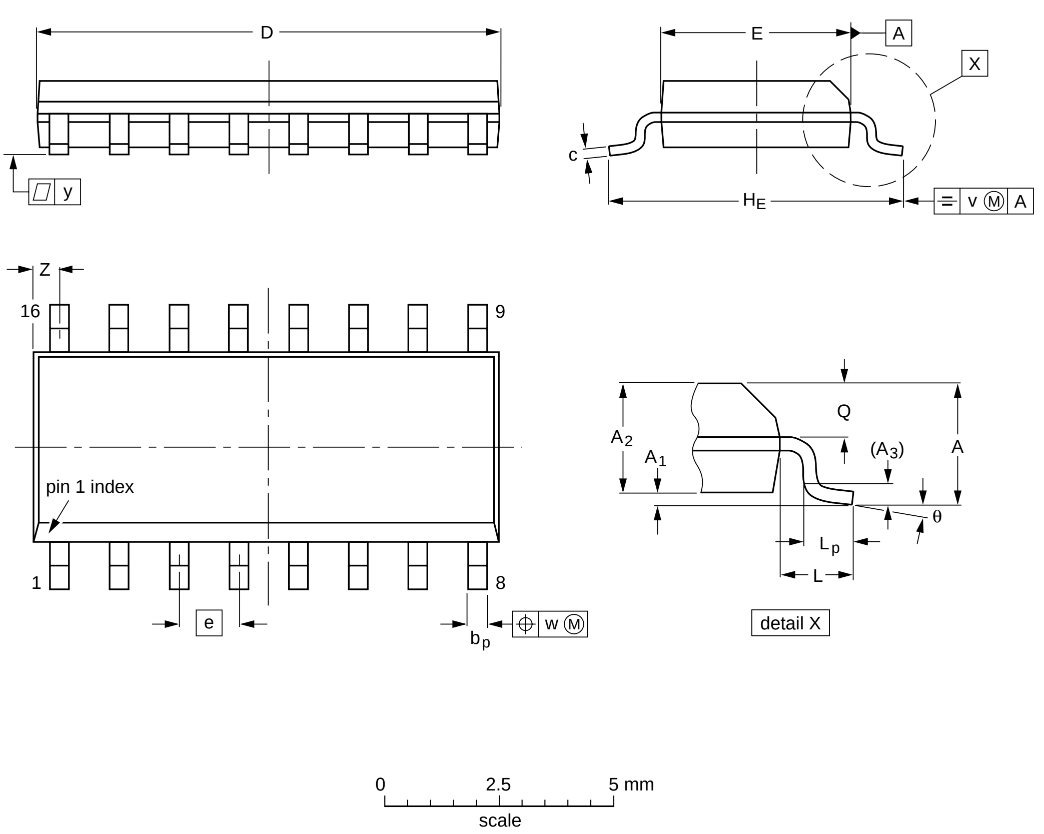
Fig 16. Test circuit for measuring switching times

Table 10. Test data

Supply voltage	Load		V_{EXT}		
V_{CC}	C_L	R_L	t_{PLH}, t_{PHL}	t_{PZH}, t_{PHZ}	t_{PZL}, t_{PLZ}
2.3 V to 2.7 V	30 pF	500 Ω	open	GND	$2V_{CC}$
3.0 V to 3.6 V	50 pF	500 Ω	open	GND	$2V_{CC}$

12. Package outline

SO16: plastic small outline package; 16 leads; body width 3.9 mm **SOT109-1**



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	10.0 9.8	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8^o 0^o
inches	0.069	0.010 0.004	0.057 0.049	0.01	0.019 0.014	0.0100 0.0075	0.39 0.38	0.16 0.15	0.05	0.244 0.228	0.041	0.039 0.016	0.028 0.020	0.01	0.01	0.004	0.028 0.012	

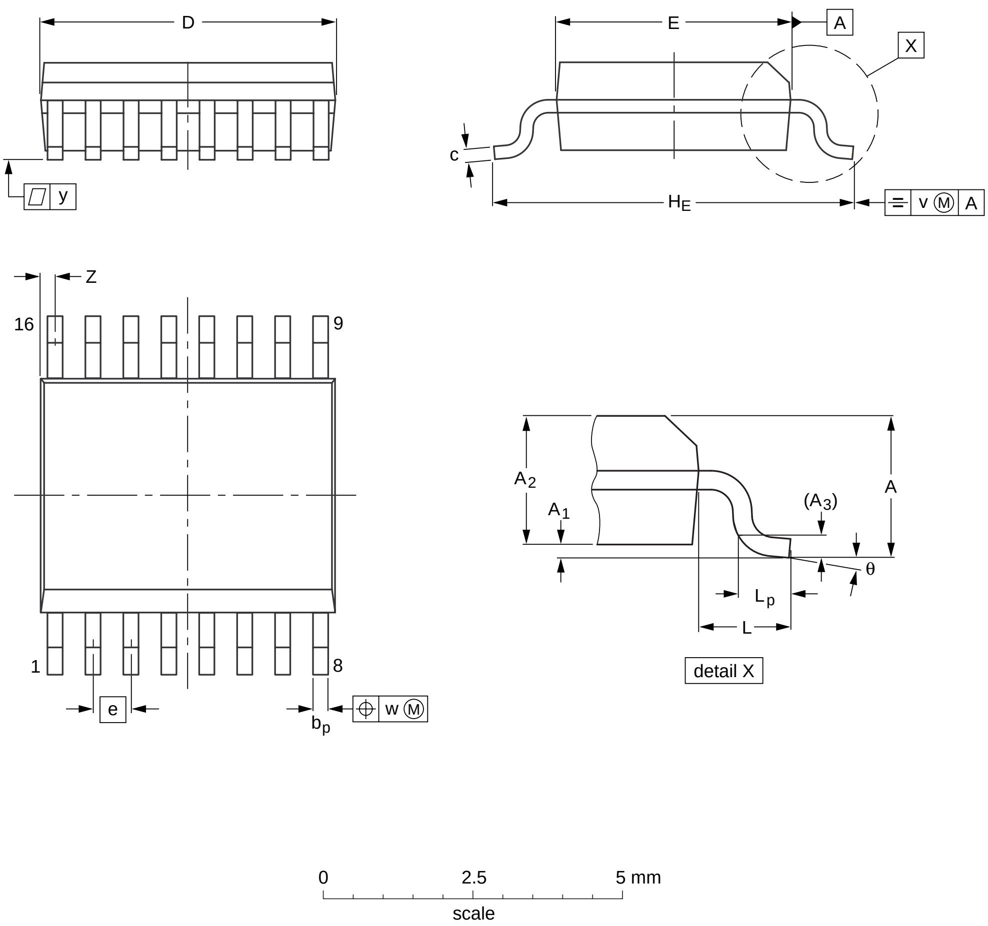
Note

1. Plastic or metal protrusions of 0.15 mm (0.006 inch) maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT109-1	076E07	MS-012				~~99-12-27~~ 03-02-19

Fig 17. Package outline SOT109-1 (SO16)

SSOP16: plastic shrink small outline package; 16 leads; body width 3.9 mm; lead pitch 0.635 mm **SOT519-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (1)	e	H_E	L	L_p	v	w	y	Z (1)	θ
mm	1.73	0.25 0.10	1.55 1.40	0.25	0.31 0.20	0.25 0.18	5.0 4.8	4.0 3.8	0.635	6.2 5.8	1	0.89 0.41	0.2	0.18	0.09	0.18 0.05	8° 0°

Note

1. Plastic or metal protrusions of 0.2 mm maximum per side are not included.

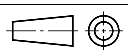
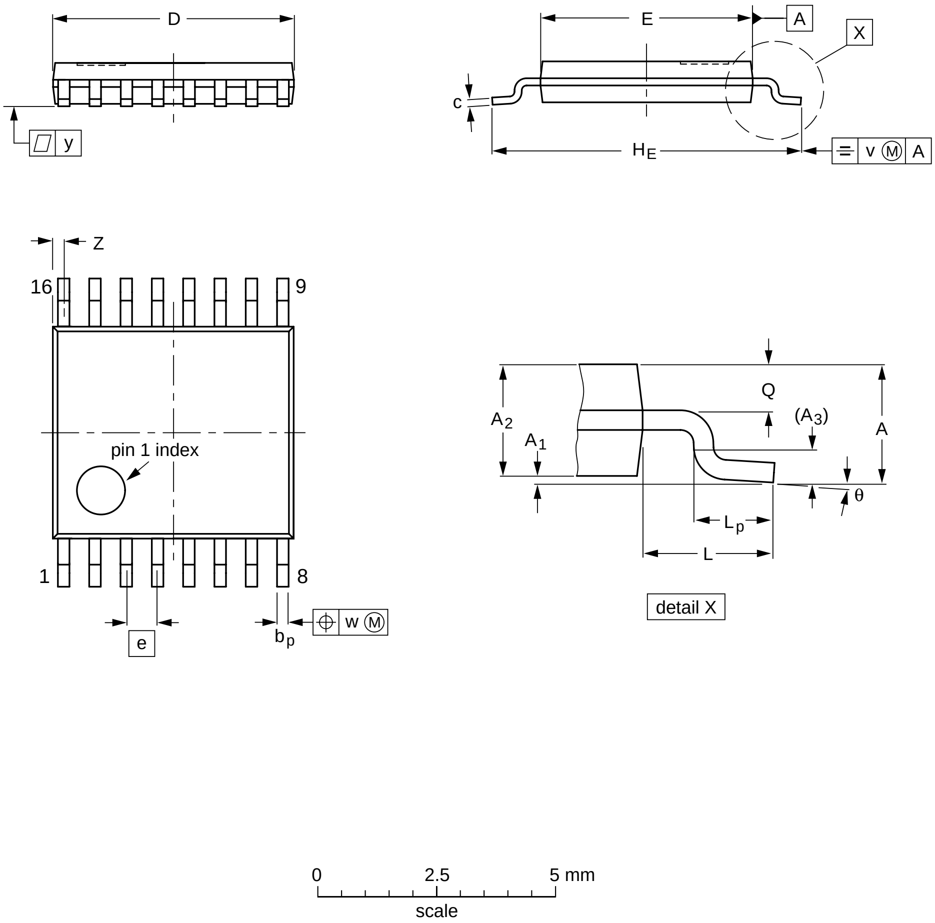
OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT519-1						~~99-05-04~~ 03-02-18

Fig 18. Package outline SOT519-1 (SSOP16)

TSSOP16: plastic thin shrink small outline package; 16 leads; body width 4.4 mm **SOT403-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A max.	A_1	A_2	A_3	b_p	c	D (1)	E (2)	e	H_E	L	L_p	Q	v	w	y	Z (1)	θ
mm	1.1	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.40 0.06	8^o 0^o

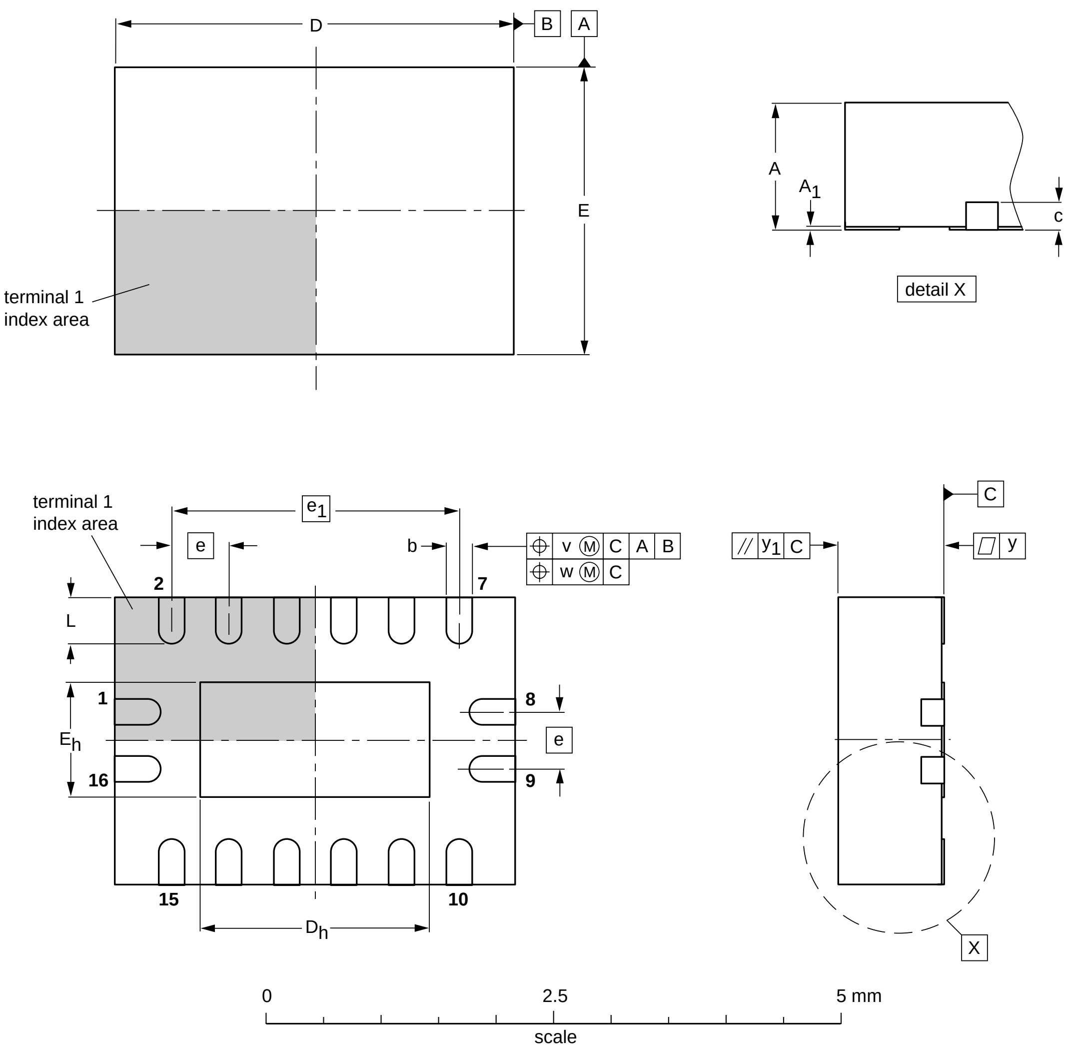
Notes

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT403-1		MO-153				~~99-12-27~~ 03-02-18

Fig 19. Package outline SOT403-1 (TSSOP16)

DHVQFN16: plastic dual in-line compatible thermal enhanced very thin quad flat package; no leads; 16 terminals; body 2.5 x 3.5 x 0.85 mm **SOT763-1**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1) max.	A_1	b	c	D(1)	D_h	E(1)	E_h	e	e_1	L	v	w	y	y_1
mm	1	0.05 0.00	0.30 0.18	0.2	3.6 3.4	2.15 1.85	2.6 2.4	1.15 0.85	0.5	2.5	0.5 0.3	0.1	0.05	0.05	0.1

Note

1. Plastic or metal protrusions of 0.075 mm maximum per side are not included.

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOT763-1	- - -	MO-241	- - -			~~02-10-17~~ 03-01-27

Fig 20. Package outline SOT763-1 (DHVQFN16)

13. Abbreviations

Table 11. Abbreviations

Acronym	Description
CDM	Charged Device Model
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

14. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74CBTLV3257_1	<tbd>	Product data sheet	-	-

15. Legal information

15.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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17. Contents

Date of release: 02 October 2009
Document identifier: 74CBTLV3257_1